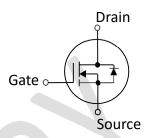


SPQ8R5N30W

30V, 10A (1) N-Channel MOSFET

- Advanced Trench Device Design and Processes
- High Reliability Capability
- 100% CP Probing and Inking

SYMBOL



Electrical Characteristics in C/P Test (T _J at 25 °C)							
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Condition	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	30	-	_	٧	$V_{GS} = 0V, I_D = 250 \mu A$	
R _{DS(ON)}	Static Drain-Source On-Resistance	_	6.5	8.5	mΩ	$V_{GS} = 10V, I_D = 1A(2)$	
R _{DS(ON)}	Static Drain-Source On-Resistance	_	8.5	14	mΩ	$V_{GS} = 4.5V, I_D = 1A(2)$	
V _{GS (th)}	Gate Threshold Voltage	1.0		2.5	>	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
I _{DSS}	Drain-to-Source Leakage Current	1	1	1	μA	V _{DS} =30V, V _{GS} =0V	
I _{GSS}	Gate-Body Leakage Current			±100	nA	V _{DS} =0V, V _{GS} =±20V	
T _J , T _{STG}	Operating and Storage Temperature	-55°C to 150°C Max.					

Mechanical Data	Die Drawing	
Chip Size	1532 µm X 940 µm	
Gate Pad Size	180 µm X 180 µm	
Source Pad Size	1314 µm X 874 µm	
Scribe Line Width	60 µm	
Wafer Thickness	150 µm	
Wafer Diameter	200 mm	
Gross Die	18012 EA	
Source Metallization	Al-Cu (4µm typical)	
Drain Metallization	Ti-Ni-Ag	
Passivation	N/A	
Recommended Storage Environment	Store in original container, in dry nitrogen, 6 months at ambient temperature of 23°C ± 3°C	

⁽¹⁾ This characteristic assumes the die is assembled in SO-8 package. Actual performance may degrade when assembled.

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⁽²⁾ Pulse Width tp = $< 300 \mu S$, Duty Cycle < 2%.

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